

- 1 -

Docket: 0756-7218

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re DIVISIONAL application of)
Shunpei YAMAZAKI et al.)
Based on Serial No. 10/214,691) Group Art Unit: 2826
Filed: August 9, 2002) Examiner: Abraham
For: SEMICONDUCTOR DEVICE AND)
METHOD OF FABRICATING SAME)

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, Virginia 22313-1450

Sir:

In accordance with the provisions of 37 C.F.R. 1.56 and 37 C.F.R. 1.97-1.99, Applicant submits herewith a Form PTO-1449 listing references known to Applicant and requests that these references be made of record in the above identified application. Copies of the references listed are submitted herewith in accordance with 37 C.F.R. 1.98(a).

The references listed on the attached Form PTO-1449 were cited in parent application Serial No. 10/214,691 and predecessor Application Serial No. 08/785,486 and copies of the references can be found in those applications.

Respectfully submitted,


Eric J. Robinson
Reg. No. 38,285
Robinson Intellectual Property Law Office
PMB 955
21010 Southbank Street
Potomac Falls, Virginia 20165
(571) 434-6789 (Voice)
(571) 434-9499 (Facsimile)

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /BTL/

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO				Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Application Number	Based on 10/214,691
				Filing Date	August 9, 2002
				First Named Inventor	Shunpei YAMAZAKI, et al.
				Group Art Unit	2826
				Examiner Name	Fetsun Abraham Benjamin
Sheet	1	of	12	Attorney Docket Number	0756-7218

T Liu

U.S. PATENT DOCUMENTS						
Examiner Initials ¹	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
/BTL/		5,686,328		Zhang et al.	11/11/97	
		5,763,899		Yamazaki et al.	06/09/98	
		5,782,665		Weisfield et al.	07/21/98	
		5,922,125		Zhang	07/13/99	
		6,083,801		Ohtani	07/04/00	
		5,744,822		Takayama et al.	04/28/98	
		5,744,824		Kousai et al.	04/28/98	
		5,766,977		Yamazaki	06/16/98	
		5,773,846		Zhang et al.	06/30/98	
		5,773,847		Hayakawa	06/30/98	
		5,773,327		Yamazaki et al.	06/30/98	
		5,795,795		Kousai et al.	08/18/98	
		5,808,321		Mitanaga et al.	09/15/98	
		3,890,632		Ham et al.	06/17/75	
		4,330,363		Biefesen et al.	05/18/82	
		4,466,073		Boyan et al.	08/14/84	
		5,543,636		Yamazaki	08/06/96	
		6,140,165		Zhang et al.	10/31/00	
		6,147,667		Yamazaki et al.	11/14/00	
		6,180,439 B1		Yamazaki et al.	01/30/01	
		5,929,527		Yamazaki et al.	07/27/99	
		5,949,107		Zhang	09/07/99	
		6,031,249		Yamazaki et al.	02/29/00	
		6,121,683		Yamazaki et al.	09/19/00	
		6,207,969 B1		Yamazaki et al.	03/27/01	

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS					
Examiner Initials ¹	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.			T ²
/BTL/		Japan J. Appl. Phys. 8 (1969) 1056, "Effect of Deposited Metals on the Crystallization Temperature of Amorphous Germanium Film," OKI et al.			
↓		Technology Information Association, "Thermo-Auto-Chrome Full Color Recording Technology," May 31, 1995			

Examiner Signature	/Benjamin Tzu-Hung Liu/	Date Considered	04/28/2008
--------------------	-------------------------	-----------------	------------

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Unique citation designation number. ² See attached Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /BTL/

Please type a plus sign (+) inside this box → [+]

PTO/SB/08A (08-00)

Approved for use through 10/31/2002. OMB 0651-0031

U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				<i>Complete if Known</i>	
				Application Number	Based on 10/214,691
				Filing Date	August 9, 2002
				First Named Inventor	Shunpei YAMAZAKI, et al.
				Group Art Unit	2826
				Examiner Name	Fetsum Abraham Benjamin T Liu
Sheet	2	of	12	Attorney Docket Number	0756-7218

U.S. PATENT DOCUMENTS						
Examiner Initials ¹	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
/BTL/		5,811,327		Funai et al.	09/22/98	
		5,818,076		Zhang et al.	10/06/98	
		5,821,138		Yamazaki et al.	10/13/98	
		5,824,574		Yamazaki et al.	10/20/98	
		6,175,348		Zhang et al.	01/16/01	
		5,728,259		Suzawa et al.	03/17/98	
		6,278,132 B1		Yamazaki et al.	08/21/01	
		5,818,076		Zhang et al.	10/06/98	
		3,389,024		Schimmer	06/18/68	
		3,783,049		Sandera	01/01/74	
		4,059,461		Fan et al.	11/22/77	
		4,068,020		Reuschel	01/10/78	
		4,132,571		Cuomo et al.	01/02/79	
		4,174,217		Flatley	11/13/79	
		4,226,898		Ovshinsky et al.	10/07/80	
		4,231,809		Schmidt	11/04/80	
		4,271,422		Ipri	06/02/81	
		4,277,884		Hsu	07/14/81	
		4,300,989		Chang	11/17/81	
		4,309,224		Shibata	01/05/82	
		4,331,709		Risch et al.	05/25/82	
		4,379,020		Glaeser et al.	04/05/83	
		4,409,724		Tasch, Jr., et al.	10/18/83	
		4,472,458		Sirinyan et al.	09/18/84	
		4,481,121		Barthel	11/06/84	
		4,534,820		Mori et al.	08/13/85	
		4,544,418		Gibbons	10/01/85	

FOREIGN PATENT DOCUMENTS							
Examiner Initials ¹	Cite No. ¹	Foreign Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ²
		Office ³	Number ⁴	Kind Code ⁵ (if known)			
/BTL/		JP	07-335900		Teramoto Satoshi	12/22/95	
/BTL/		JP	64-081324			03/27/89	Abst.
							Abst.

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials ¹	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
/BTL/		IBM Technical Disclosure Bulletin, Vol. 11, No.7, A.R. Baker, Jr.	

Examiner Signature	/Benjamin Tzu-Hung Liu/	Date Considered	04/28/2008
--------------------	-------------------------	-----------------	------------

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /BTL/

Please type a plus sign (+) inside this box → [+]

PTO/SB/08A (08-00)

Approved for use through 10/31/2002. OMB 0651-0031

U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO				<i>Complete if Known</i>	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Application Number	Based on 10/214,691
Sheet	3	of	12	Filing Date	August 9, 2002
				First Named Inventor	Shunpei YAMAZAKI, et al.
				Group Art Unit	2826
				Examiner Name	Petsum Abraham Benjamin
				Attorney Docket Number	T Liu 0756-7218

T Liu

U.S. PATENT DOCUMENTS						
Examiner Initials ¹	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
/BTL/		4,546,376		Nakata et al.	10/08/85	
		4,597,160		Ipri	07/01/86	
		4,634,473		Swartz et al.	01/06/87	
		4,735,824		Yamabe et al.	04/05/88	
		4,755,481		Faraone	07/05/88	
		4,911,781		Fox et al.	03/27/90	
		4,959,247		Moser et al.	09/25/90	
		4,959,700		Yamazaki	09/25/90	
		4,996,077		Mosiehi et al.	02/26/91	
		4,996,523		Bell et al.	02/26/91	
		5,043,224		Jaccodine et al.	08/27/91	
		5,075,259		Moran	12/24/91	
		5,089,441		Mosiehi	02/18/92	
		5,112,764		Mitra et al.	05/12/92	
		5,145,808		Sameshima et al.	09/08/92	
		5,147,826		Liu et al.	09/15/92	
		5,173,446		Asakawa et al.	12/22/92	
		5,200,630		Nakamura et al.	04/06/93	
		5,221,423		Sugino et al.	06/22/93	
		5,225,355		Sugino et al.	07/06/93	
		5,244,836		Lim	09/14/93	
		5,254,480		Tran	10/19/93	
		5,262,350		Yamazaki et al.	11/16/93	
		5,262,654		Yamazaki	11/16/93	
		5,275,851		Fonash et al.	01/04/94	
		5,278,093		Yonehara	01/11/94	
		5,289,030		Yamazaki et al.	02/22/94	
		5,296,405		Yamazaki et al.	03/22/94	
		5,298,075		Lagendijk et al.	03/29/94	
		5,308,998		Yamazaki et al.	05/03/94	
		5,313,075		Zhang et al.	05/17/94	
		5,352,291		Zhang et al.	10/04/94	
		5,354,697		Oostra et al.	10/11/94	
		5,358,907		Wong	10/25/94	
		5,366,926		Mei et al.	11/22/94	
		5,387,530		Doyle et al.	02/07/95	
		5,424,230		Wakai	06/13/95	

Examiner Signature	/Benjamin Tzu-Hung Liu/	Date Considered	04/28/2008
--------------------	-------------------------	-----------------	------------

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /BTL/

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO

Complete if Known

INFORMATION DISCLOSURE
STATEMENT BY APPLICANT

(use as many sheets as necessary)

Application Number	Based on 10/214,691
Filing Date	August 9, 2002
First Named Inventor	Shunpei YAMAZAKI, et al.
Group Art Unit	2826
Examiner Name	Fetsum Abraham Benjamin

T Liu

Sheet

4

of

12

Attorney Docket Number

0756-7218

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
/BTL/		5,470,763		Hamada	11/28/95	
		5,480,811		Chiang et al.	01/02/96	
		5,504,019		Miyasaka et al.	04/02/96	
		5,508,207		Horai et al.	04/16/96	
		5,531,182		Yonehara	07/02/96	
		5,580,815		Hsu et al.	12/03/96	
		5,621,244		Yamazaki et al.	04/15/97	
		5,661,311		Takemura et al.	08/26/97	
		5,684,317		Hwang	11/04/97	
		5,684,365		Tang et al.	11/04/97	
		5,693,541		Yamazaki et al.	12/02/97	
		5,696,003		Makita et al.	12/09/97	
		5,717,224		Zhang	02/10/98	
		5,734,179		Chang et al.	03/31/98	
		5,773,327		Yamazaki et al.	06/30/98	
		5,786,796		Takayama et al.	07/28/98	
		5,821,560		Arai et al.	10/13/98	
		5,828,429		Takemura	10/27/98	
		5,838,508		Sugawara	11/17/98	
		5,843,225		Takayama et al.	12/01/98	
		5,846,857		Ju	12/08/98	
		5,849,611		Yamazaki et al.	12/15/98	
		5,882,960		Zhang et al.	03/16/99	
		5,888,858		Yamazaki et al.	03/30/99	
		5,895,933		Zhang et al.	04/20/99	
		5,899,547		Yamazaki et al.	05/04/99	
		5,929,464		Yamazaki et al.	07/27/99	
		5,933,205		Yamazaki et al.	08/03/99	
		5,940,732		Zhang	08/17/99	
		5,962,869		Yamazaki et al.	10/05/99	
		5,963,278		Yamazaki et al.	10/05/99	
		5,985,740		Yamazaki et al.	11/16/99	
		5,990,491		Zhang	11/23/99	
		5,990,542		Yamazaki	11/23/99	
		6,005,648		Zhang et al.	12/21/99	
		6,011,277		Yamazaki	01/04/00	

Examiner Signature	/Benjamin Tzu-Hung Liu/	Date Considered	04/28/2008
--------------------	-------------------------	-----------------	------------

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /BTL/

Please type a plus sign (+) inside this box → [+]

10712062 GAU: 2826
TO/SB/08A (08-00)

Approved for use through 10/31/2002. OMB 0651-0031

U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

<p>Substitute for form 1449A/PTO</p> <p>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</p> <p><i>(use as many sheets as necessary)</i></p>				Complete if Known			
				Application Number		Based on 10/214,691	
				Filing Date		August 9, 2002	
				First Named Inventor		Shunpei YAMAZAKI, et al.	
				Group Art Unit		2826	
				Examiner Name	Fetsum Abramany Benjamin T Liu		
Sheet	5	of	12	Attorney Docket Number	0756-7218		

U.S. PATENT DOCUMENTS						
Examiner Initials ¹	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
/BTL/		6,013,929		Ohtani	01/11/00	
		6,048,758		Yamazaki et al.	04/11/00	
		6,063,654		Ohtani	05/16/00	
		6,077,731		Yamazaki et al.	06/20/00	
		6,093,934		Yamazaki et al.	07/25/00	
		6,100,562		Yamazaki et al.	08/08/00	
		RE 28,385		Mayer	04/08/75	
		RE 28,386		Heiman et al.	04/08/75	

FOREIGN PATENT DOCUMENTS							
Examiner Initials ¹	Cite No. ¹	Foreign Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁴
		Office ³	Number ⁴	Kind Code ⁵ (if known)			
/BTL/		EP	0 178 447		10/09/84		English
		JP	01-187814		07/27/89		Full
		JP	01-187874		07/27/89		Abst.
		JP	01-187875		07/27/89		Abst.
		JP	01-206632		08/18/89		Abst.
		JP	02-140915		05/30/90		Full
		JP	02-148687		06/07/90		Abst.
		JP	02-275641		11/09/90		Abst.
		JP	03-280418		12/11/91		Abst.
		JP	03-280420		12/11/91		Full
		JP	05-082442		04/02/93		Abst.
		JP	05-107561		04/30/93		Abst.
		JP	05-299348		11/12/93		Abst.
		JP	06-232059		08/19/94		Full
		JP	07-161634		06/23/95		Abst.
		JP	07-321339		12/08/95		Abst.
		JP	08-129358		05/21/96		Abst.
		JP	08-129359		05/21/96		Abst.
		JP	08-129360		05/21/96		Abst.
		JP	08-234683		09/13/96		Abst.
		JP	08-241047		09/17/96		Abst.
		JP	08-241048		09/17/96		Abst.
		JP	08-241057		09/17/96		Abst.
		JP	08-241997		09/17/96		Abst.
		JP	60-105216		06/10/85		Full
		JP	61-063017		04/01/86		Full
		JP	61-063107		04/01/86		Abst.
		JP	62-169356		07/25/87		Abst.

Examiner Signature	/Benjamin Tzu-Hung Liu/	Date Considered	04/28/2008
--------------------	-------------------------	-----------------	------------

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /BTL/

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO				<i>Complete if Known</i>	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Application Number	Based on 10/214,691
				Filing Date	August 9, 2002
				First Named Inventor	Shunpei YAMAZAKI, et al.
				Group Art Unit	2826
				Examiner Name	Fetsum Abraham Benjamin T Liu
Sheet	6	of	12	Attorney Docket Number	0756-7218

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
/BTL/		Caune et al., "Combined CW Laser and Furnace Annealing of Amorphous Si and Ge in Contact With Some Metals," January 1, 1989, pp. 597-604, Applied Surface Science, Vol. 36	
		Stoemnos et al., "Crystallization of Amorphous Silicon by Reconstructive Transformation Utilizing Gold," March 18, 1991, pp. 1196-1198, Appl. Phys. Lett. 58(11)	
		Kakkad et al., "Crystallized Si-Films By Low-Temperature Rapid Thermal Annealing of Amorphous Silicon," March 1, 1989, pp. 2069-2072, J. Appl. Phys. 65(5)	
		Oki et al., "Effect of Deposited Metals On The Crystallization Temperature of Amorphous Germanium Film," 1969, pp. 1056, Jpn. J. Appl. Phys. 8	
		Kuznetsov et al., "Enhanced Solid Phase Epitaxial Recrystallization of Amorphous Silicon Due to Nickel Silicide Precipitation Resulting From Ion Implantation and Annealing," 1993, pp. 990-993, Nucl. Instruments Methods Physics Research, 880/881	
		Hayashi et al., "Fabrication of Low-Temperature Bottom Gate Poly-Si TFTs on Large Area Substrate by Linear-Beam Excimer Laser Crystallization and Ion Doping Method," January 1, 1995, pp. 829-832, IEEE IEDM	
		Takenaka et al., "High Mobility Poly-Si Thin Film Transistors Using Solid Phase Crystallized a-Si Films Deposited by Plasma Enhanced Chemical Vapor Deposition," December 1990, pp. L2380-L2383, Jpn. J. Appl. Phys. Vol 29, No. 12	
		Hatalis et al., "High Performance Thin-Film Transistors in Low Temperature Crystallized LPCVD Amorphous Silicon Films," August 1987, pp. 361-364, Elec. Dev. Letters Vol. EDL 8, No. 8	
		Zorabedian et al., "Lateral Seeding of Silicon-on-Insulator Using an Elliptical Laser Beam: A Comparison of Scanning Methods," 1984, pp. 81-86, Mat. Res. Soc. Symp. Proc. Vol. 33	
		Green et al., "Method to Purify Semiconductor Wafers," October 1973, pp. 1612-1613, IBM Tech. Discl. Bulletin, Vol. 16, No. 5	
		Boyd, et al., "Oxidation of Silicon Surfaces by CO ₂ Lasers," July 15, 1982, pp. 162-164, Applied Phys. Letters, Vol. 41, No. 2	
↓		Wolf et al., "Silicon Processing for the VLSI Era Volume 1: Process Technology," 1986, pp. 215-216, Lattice Press	

Examiner Signature	/Benjamin Tzu-Hung Liu/	Date Considered	04/28/2008
--------------------	-------------------------	-----------------	------------

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /BTL/

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO				<i>Complete if Known</i>	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Application Number	Based on 10/214,691
				Filing Date	August 9, 2002
				First Named Inventor	Shunpei YAMAZAKI, et al.
				Group Art Unit	2826
				Examiner Name	Petsum Abraham Benjamin T. Liu
Sheet	7	of	12	Attorney Docket Number	0756-7218

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS				
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.		T ²
/BTL/		Lau et al., "Solid Phase Epitaxy in Silicide Forming System," 1977, pp. 313-322, Thin Solid Films, 47		
		Kawazu et al., "Low-Temperature Crystallization of Hydrogenated Amorphous Silicon Induced by Nickel Silicide Formation," December 1990, pp. 2698-2704, Inst. Of Appl. Phys. Vol. 29, No. 12		
		Wolf et al., "Silicon Processing for the VLSI Era Volume 1 – Process Technology," 1986, pp. 550-551, Lattice Press		
		Bruines et al., "Between Explosive Crystallization and Amorphous Regrowth: Inhomogeneous Solidification Upon Pulsed Laser Annealing of Amorphous Silicon," March 1, 1987, pp. 507-509, Applied Physics Letter, Vol. 50		
		Kawazu et al., "Initial Stage of the Interfacial Reaction between Nickel and Hydrogenated Amorphous Silicon," April 1, 1990, pp. 729-738, Japanese Journal of Appl. Phys., Vol.29		
		Kakkad et al., "Low Temperature Selective Crystallization of Amorphous Silicon," 1989, pp. 66-68, Journal of Non-Crystalline Solids, 115		
		Suresh et al., "Electroless Plated Nickel Contacts to Hydrogenated Amorphous Silicon," January 1, 1994, pp. 78-81, Thin Solids Films, Vol. 252		
		Sakaguchi et al., "Current Progress in Epitaxial Layer Transfer," March 1, 1997, pp. 378-387, IEICE Trans. Electron, Vol. E80 C/No. 3		
		Kouvatsos et al., "Fluorine-Enhanced Oxidation of Polycrystalline Silicon and Application to Thin-Film Transistor Fabrication," August 24, 1992, pp. 937-939, Appl. Phys. Letter, Vol. 61, No. 8		
		Sze, "VLSI Technology," January 1, 1988, pp. 397-400, McGraw-Hill Publishing Company, Second Edition		
		Ghandhi, "VLSI Fabrication Principles," January 1, 1983, pp. 419-429, Wiley and Sons		
		Kuper et al., "Effects of Fluorine Implantation on the Kinetics of Dry Oxidation of Silicon," August 1, 1986, pp. 985-990, J. Applied Physics		
↓		Wolf et al., "Silicon Processing for the VLSI Era Volume 1: Process Technology," 1986, pp. 198-207, Lattice Press		

Examiner Signature	/Benjamin Tzu-Hung Liu/	Date Considered	04/28/2008
--------------------	-------------------------	-----------------	------------

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /BTL/

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO				<i>Complete if Known</i>	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Application Number	Based on 10/214,691
				Filing Date	August 9, 2002
				First Named Inventor	Shunpei YAMAZAKI, et al.
				Group Art Unit	2826
				Examiner Name	Fetsum Abraham Benjamin T Liu
Sheet	8	of	12	Attorney Docket Number	0756-7218

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials ¹	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
/BTL/		Thompson et al., "Silicide Formation in Pd-a-Si:H Schottky Barriers," August 1981, pp. 274-276, Appl. Phys. Lett., Vol. 39, No. 3	
		Nemanich et al., "Initial Phase Formation at the Interface of Ni, Pd, or Pt and Si," 1984, pp. unknown, Mat. Res. Soc. Symp. Proc., Vol. 25	
		Nemanich et al., "Structure and Growth of the Interface of Pd on a-SiH," June 15, 1981, pp. 6828-6831, The American Physical Society Physics Review, Vol. 22, No. 12	
		Hemple et al., "Needle-Like Crystallization of Ni Doped Amorphous Silicon Thin Film," 1993, pp. 921-924, Solid State Communications, Vol. 85, No. 11	
		Kuo, "Thin Film Transistor Technologies," Vol. 94-35, pp. 116-122, The Electrochemical Society Proceedings	
		Author Unknown, "Thermo Auto-Chrome Full Color Recording Technology," May 31, 1995, pp. Unknown, Technology Information Association	
		Wolf et al., "Thermal Oxidation of Single Crystal Silicon," 1986, pp. 207-211, Silicon Processing for the VLSI Era	
		Erokhin et al., "Spatially Confined Nickel Disilicide Formation at 400C on Ion Implantation Preamorphized Silicon," Dec. 6, 1993, pp. 3173-3175, Appl. Phys. Lett. 63 (23)	
		Dvurechenskii et al., "Transport Phenomena in Amorphous Silicon Doped by Ion Implantation of 3d Metals," 1986, pp. 635-640, Akademikian Lavrentev Prospekt 13, 630090 Novosibirsk 90, USSR	
		Batstone et al., "Microscopic Processes in Crystallization," January 1, 1994, pp. 257-268, Solid State Phenomena, Vol. 37-38	
		Cammarata et al., "Silicide Precipitation and Silicon Crystallization in Nickel Implanted Amorphous Silicon Thin Films," Oct 10, 1990, pp. 2133-2138, J. Mater. Res. Vol. 5, No. 10	
↓		Hayzelden et al., "Silicide Formation and Silicide Mediated Crystallization of Nickel-Implanted Amorphous Silicon Thin Films," May 15, 1993, pp. 8279-8289, J. Appl. Phys. 73(12)	

Examiner Signature	/Benjamin Tzu-Hung Liu/	Date Considered	04/28/2008
--------------------	-------------------------	-----------------	------------

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /BTL/

Please type a plus sign (+) inside this box → [+]

10712062 GAU: 2826
PTO/SB/08A (08-00)

Approved for use through 10/31/2002. OMB 0651-0031

U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO				<i>Complete if Known</i>	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Application Number	Based on 10/214,691
				Filing Date	August 9, 2002
				First Named Inventor	Shunpei YAMAZAKI, et al.
				Group Art Unit	2826
				Examiner Name	Peisum Abraham Benjamin T. Liu
Sheet	9	of	12	Attorney Docket Number	0756-7218

U.S. PATENT DOCUMENTS						
Examiner Initials	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
/BTL/		5,705,829		Miyanaga et al.	01/06/98	
		5,712,191		Nakajima et al.	01/27/98	
		5,756,364		Tanaka et al.	05/26/98	
		5,619,044		Makita et al.	04/08/97	
		5,530,266		Yonehara et al.	06/25/96	
		5,550,070		Funai et al.	08/27/96	
		5,693,959		Inoue et al.	12/02/97	

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
/BTL/		Kuznetsov et al., "Silicide Precipitate Formation and Solid Phase Re-Growth of Ni-Implanted Amorphous Silicon," April 5-8, 1993, pp. 191-194, Inst. Phys. Conf. Ser. No. 134.4: Proceedings of Royal Microscopical Society Conf.	
		Liu et al., "Polycrystalline Silicon Thin Film Transistors on Corning 7059 Glass Substrates Using Short Time, Low-Temperature Processing," May 17, 1993, pp. 2554-2556, Appl. Phys. Lett 62(20)	
		Liu et al., "Selective Area Crystallization of Amorphous Silicon Films by Low-Temperature Rapid Thermal Annealing," August 14, 1989, pp. 660-662, Appl. Phys. Lett 55(7)	
		Spaepen et al., Metal-Enhanced Growth of Silicon, 1992, pp. 483-499, Crucial Issues in Semiconductor Materials & Processing Technologies	

Examiner Signature	/Benjamin Tzu-Hung Liu/	Date Considered	04/28/2008
--------------------	-------------------------	-----------------	------------

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /BTL/

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO				<i>Complete if Known</i>	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Application Number Based on 10/214,691	
				Filing Date August 9, 2002	
				First Named Inventor Shunpei YAMAZAKI, et al.	
				Group Art Unit 2826	
				Examiner Name Tetsunari Abraham Benjamin	
Sheet	10	of	12	Attorney Docket Number 0756-7218	

T Liu

U.S. PATENT DOCUMENTS					
Examiner Initials ¹	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY
		Number	Kind Code ² (if known)		
/BTL/		5,403,772		Zhang et al.	04/04/95
		5,426,064		Zhang et al.	06/20/95
		5,481,121		Zhang et al.	01/02/96
		5,488,000		Zhang et al.	01/30/96
		5,492,843		Adachi et al.	02/20/96
		5,501,989		Takayama et al.	03/26/96
		5,508,533		Takemura	04/16/96
		5,529,937		Zhang et al.	06/25/96
		5,534,716		Takemura	07/09/96
		5,543,352		Ohtani et al.	08/06/96
		5,563,426		Zhang et al.	10/08/96
		5,569,610		Zhang et al.	10/29/96
		5,569,936		Zhang et al.	10/29/96
		5,580,792		Zhang et al.	12/03/96
		5,585,291		Ohtani et al.	12/17/96
		5,589,694		Takayama et al.	12/31/96
		5,595,923		Zhang et al.	01/21/97
		5,595,944		Zhang et al.	01/21/97
		5,604,360		Zhang et al.	02/18/97
		5,605,846		Ohtani et al.	02/25/97
		5,606,179		Yamazaki et al.	02/25/97
		5,608,232		Yamazaki et al.	03/04/97
		5,612,250		Ohtani et al.	03/18/97
		5,614,426		Funada et al.	03/25/97
		5,614,733		Zhang et al.	03/25/97
		5,616,506		Takemura	04/01/97
		5,620,910		Teramoto	04/15/97
		5,621,224		Yamazaki et al.	04/15/97
		5,624,851		Takayama et al.	04/29/97
		5,637,515		Takemura	06/10/97
		5,639,698		Yamazaki et al.	06/17/97
		5,643,826		Ohtani et al.	07/01/97
		5,646,424		Zhang et al.	07/08/97
		5,654,203		Ohtani et al.	08/05/97
		5,656,825		Kusumoto et al.	08/12/97
		5,663,077		Adachi et al.	09/02/97
		5,677,549		Takayama et al.	10/14/97
		5,696,386		Yamazaki	12/09/97
		5,696,388		Funada et al.	12/09/97
		5,700,333		Yamazaki et al.	12/23/97

Examiner Signature	/Benjamin Tzu-Rung Liu/	Date Considered	04/28/2008
--------------------	-------------------------	-----------------	------------

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /BTL/

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO				<i>Complete if Known</i>	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Application Number	Based on 10/214,691
				Filing Date	August 9, 2002
				First Named Inventor	Shunpei YAMAZAKI, et al.
				Group Art Unit	2826
				Examiner Name	Tetsuji Abraham Benjamin T. Liu
Sheet	11	of	12	Attorney Docket Number	0756-7218

U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
/BTL/	5,932,893			Miyanaga et al.	08/03/99	
	4,759,610			Yanagisawa	07/26/88	
	5,535,471			Guldi	07/16/96	
	5,661,056			Takeuchi	08/26/97	
	4,140,548			Zimmer	02/20/79	
	5,210,050			Yamazaki et al.	05/11/93	
	5,298,075			Lagendijk et al.	03/29/94	
	5,306,651			Masumo et al.	04/26/94	
	5,313,076			Yamazaki et al.	05/17/94	
	5,365,080			Yamazaki et al.	11/15/94	
	5,372,860			Fehlner et al.	12/13/94	
	5,591,988			Arai et al.	01/07/97	
	5,893,730			Yamazaki et al.	04/13/99	
	5,913,111			Kataoka et al.	06/15/99	
	5,953,597			Kusumoto et al.	09/14/99	
	6,011,275			Ohtani et al.	01/04/00	
	6,133,073			Yamazaki et al.	10/17/00	

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
/BTL/		Wolf, <i>Silicon Processing for the VLSI Era</i> , Volume 2, Chapter 4, page 274 (1990).	

Examiner Signature	/Benjamin Tzu-Hung Liu/	Date Considered	04/28/2008
--------------------	-------------------------	-----------------	------------

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Unique citation designation number. ² See attached Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

¹ Unique citation designation number. ² Applicant is to place a check mark here if English language Translation is attached.

Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, DC 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, Washington, DC 20231.

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

<p>Substitute for form 1449A/PTO</p> <p>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</p> <p><i>(use as many sheets as necessary)</i></p>				<i>Complete if Known</i>	
				Application Number	Based on 10/214,691
				Filing Date	August 9, 2002
				First Named Inventor	Shunpei YAMAZAKI, et al.
				Group Art Unit	2826
				Examiner Name	Fetsuni Abraham <i>Benjamin T Liu</i>
Sheet	12	of	12	Attorney Docket Number	0756-7218

U.S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

Examiner Initials ¹	Cite No. ¹	Foreign Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Office ³	Number ⁴ (if known)				
BTU	JP	06-314785			11/08/94		Ab
	JP	06-314787			11/08/94		Ab

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²

Examiner Signature	/Benjamin Tzu-Hung Liu/	Date Considered	04/28/2008
-----------------------	-------------------------	--------------------	------------

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Unique citation designation number. ² See attached Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

¹ Unique citation designation number. ² Applicant is to place a check mark here if English language Translation is attached.

Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, DC 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, Washington, DC 20231.

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /BTL/